

AMENDMENT TO THE ABSTRACT

The following abstract will replace all prior versions of the abstract in the application:

A method of producing a device with a ferroelectric crystal thin film on a first substrate ~~comprises~~including the steps of providing a ferroelectric crystal, of irradiating a first surface of ~~said the~~ ferroelectric crystal with ions so that a damaged layer is created underneath ~~said the~~ first surface, of bonding a block of material including ~~said the~~ first substrate to ~~said the~~ ferroelectric crystal to create a bonded element, wherein an interface is formed between ~~said the~~ first surface and a second surface of ~~said the~~ block, and of heating the bonded element and separating it at the damaged layer, so that a ferroelectric crystal layer remains supported by the first substrate. By this method, very thin films – down to thicknesses of a fraction of a micrometer – of ferroelectric crystals may be fabricated without jeopardizing the monocrystalline structure. ~~According to a preferred embodiment, prior to bonding the block to the second substrate, the first substrate is provided with a electrode layer prior to the bonding. In this way, a thin ferroelectric crystal layer may even be subjected to an applied voltage by electrodes.~~

(Fig. 1)